

Adem Tataroglu

List of Publications by Year in descending order

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103
papers

3,335
citations

109137

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182168

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104
all docs

104
docs citations

104
times ranked

1503
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of admittance measurements of Al/Gr-PVA/p-Si (MPS) structure. Journal of Physics and Chemistry of Solids, 2022, 169, 110861.	1.9	19
2	The photo-electrical performance of the novel CuAlMnFe shape memory alloy film in the diode application. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 264, 114931.	1.7	10
3	Compare Study on Electrical Properties of MS Diodes with and Without CoFe ₂ O ₄ -PVP Interlayer. Journal of Inorganic and Organometallic Polymers and Materials, 2021, 31, 1668-1675.	1.9	23
4	Electrical characterization of Au/n-Si (MS) diode with and without graphene-polyvinylpyrrolidone (Gr-PVP) interface layer. Journal of Materials Science: Materials in Electronics, 2021, 32, 3451-3459.	1.1	19
5	Frequency dependence of the dielectric properties of Au/(NG:PVP)/n-Si structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 7657-7670.	1.1	25
6	Complex dielectric permittivity, electric modulus and electrical conductivity analysis of Au/Si ₃ N ₄ /p-GaAs (MOS) capacitor. Journal of Materials Science: Materials in Electronics, 2021, 32, 11418-11425.	1.1	21
7	Photoresponse characteristics of Au/(CoFe ₂ O ₄ -PVP)/n-Si/Au (MPS) diode. Journal of Materials Science: Materials in Electronics, 2021, 32, 15732-15739.	1.1	27
8	A systematic influence of Cu doping on structural and opto-electrical properties of fabricated Yb ₂ O ₃ thin films for Al/Cu-Yb ₂ O ₃ /p-Si Schottky diode applications. Inorganic Chemistry Communication, 2021, 129, 108646.	1.8	18
9	Double-exponential current-voltage (I-V) behavior of bilayer graphene-based Schottky diode. Physica Scripta, 2021, 96, 125836.	1.2	2
10	Investigation of structural, kinetics and electrical properties of CuAlMnZn shape memory alloy “ p-type silicon Schottky diode. Sensors and Actuators A: Physical, 2021, 331, 112908.	2.0	5
11	Electrical, kinetic and photoelectrical properties of CuAlMnMg shape memory alloy/n-Si Schottky diode. Journal of Alloys and Compounds, 2021, 888, 161600.	2.8	15
12	Effects of temperature and frequency on capacitance and conductance characteristics of zinc-oxide based MIS-Structure. Physica B: Condensed Matter, 2020, 576, 411721.	1.3	6
13	Comparison of electrical properties of MS and MPS type diode in respect of (In ₂ O ₃ -PVP) interlayer. Physica B: Condensed Matter, 2020, 576, 411733.	1.3	46
14	Impedance spectroscopy of Au/TiO ₂ /n-Si metal-insulator-semiconductor (MIS) capacitor. Physica B: Condensed Matter, 2020, 580, 411945.	1.3	11
15	CuAlMnV shape memory alloy thin film based photosensitive diode. Materials Science in Semiconductor Processing, 2020, 107, 104858.	1.9	15
16	Current-voltage analyses of Graphene-based structure onto Al ₂ O ₃ /p-Si using various methods. Vacuum, 2020, 181, 109654.	1.6	18
17	Ionizing radiation effects on Au/TiO ₂ /n-Si metal-insulator-semiconductor (MIS) structure. Journal of Materials Science: Materials in Electronics, 2020, 31, 19846-19851.	1.1	4
18	Electrical properties of Graphene/Silicon structure with Al ₂ O ₃ interlayer. Journal of Materials Science: Materials in Electronics, 2020, 31, 9719-9725.	1.1	18

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19	Electrical characterization of silicon nitride interlayer-based MIS diode. Journal of Materials Science: Materials in Electronics, 2020, 31, 9888-9893.	1.1	14
20	Electrical and photoresponse properties of CoSO ₄ -PVP interlayer based MPS diodes. Journal of Materials Science: Materials in Electronics, 2020, 31, 11665-11672.	1.1	22
21	C-V-f and G/f ² -V-f characteristics of Au/(In ₂ O ₃ -PVP)/n-Si (MPS) structure. Physica B: Condensed Matter, 2020, 582, 411996.	1.3	33
22	Electrical Properties of MOS Capacitor with TiO ₂ /SiO ₂ Dielectric Layer. Silicon, 2020, 12, 2879-2883.	1.8	5
23	Metallo-Phthalocyanines Based Photocapacitors. Silicon, 2019, 11, 1275-1286.	1.8	6
24	A comparative study on the electrical and dielectric properties of Al/Cd-doped ZnO/p-Si structures. Journal of Materials Science: Materials in Electronics, 2019, 30, 12122-12129.	1.1	35
25	Frequency dependent dielectric properties of atomic layer deposition grown zinc-oxide based MIS structure. Physica B: Condensed Matter, 2019, 568, 31-35.	1.3	6
26	Double-exponential current-voltage (I-V) and negative capacitance (NC) behavior of Al/(CdSe-PVA)/p-Si/Al (MPS) structure. Journal of Materials Science: Materials in Electronics, 2019, 30, 9572-9581.	1.1	19
27	Dielectric, modulus and conductivity studies of Au/PVP/n-Si (MPS) structure in the wide range of frequency and voltage at room temperature. Journal of Materials Science: Materials in Electronics, 2019, 30, 6853-6859.	1.1	36
28	Electrical characteristics analyses of zinc-oxide based MIS structure grown by atomic layer deposition. Materials Research Express, 2019, 6, 026309.	0.8	15
29	Cu-Al-Mn shape memory alloy based Schottky diode formed on Si. Physica B: Condensed Matter, 2019, 560, 261-266.	1.3	14
30	Electrical and impedance properties of MPS structure based on (Cu ₂ O-Cu-PVA) interfacial layer. Journal of Materials Science: Materials in Electronics, 2018, 29, 8234-8243.	1.1	41
31	The effect of thickness on the optical, structural and electrical properties of ZnO thin film deposited on n-type Si. Journal of Molecular Structure, 2018, 1165, 376-380.	1.8	15
32	A shape memory alloy based on photodiode for optoelectronic applications. Journal of Alloys and Compounds, 2018, 743, 227-233.	2.8	18
33	Frequency-Dependent Dielectric Parameters of Au/TiO ₂ /n-Si (MIS) Structure. Silicon, 2018, 10, 2071-2077.	1.8	33
34	Structural, Electrical and Photoresponse Properties of Si-based Diode with Organic Interfacial Layer Containing Novel Cyclotriphosphazene Compound. Silicon, 2018, 10, 683-691.	1.8	16
35	Optical, Electrical and Photoresponse Properties of Si-based Diodes with NiO-doped TiO ₂ Film Prepared by Sol-gel Method. Silicon, 2018, 10, 913-920.	1.8	17
36	Ruthenium(II) Complex Based Photodiode for Organic Electronic Applications. Journal of Electronic Materials, 2018, 47, 828-833.	1.0	35

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37	On the conduction mechanisms of Au/(Cu ₂ O@Cu@PVA)/n-Si (MPS) Schottky barrier diodes (SBDs) using current-voltage-temperature (I-V-T) characteristics. Journal of Materials Science: Materials in Electronics, 2018, 29, 159-170.	1.1	73
38	Analysis of interface states in Au/ZnO/p-InP (MOS) structure. Journal of Materials Science: Materials in Electronics, 2018, 29, 12553-12560.	1.1	36
39	Forward and reverse bias current-voltage (I-V) characteristics in the metal-ferroelectric-semiconductor (Au/SrTiO ₃ /n-Si) structures at room temperature. Journal of Materials Science: Materials in Electronics, 2018, 29, 16740-16746.	1.1	27
40	Analysis of barrier inhomogeneities in AuGe/n-Ge Schottky diode. Indian Journal of Physics, 2018, 92, 1397-1402.	0.9	16
41	Boron doped graphene based linear dynamic range photodiode. Physica B: Condensed Matter, 2018, 545, 86-93.	1.3	25
42	Electronic and optoelectronic properties of Al/coumarin doped Pr ₂ Se ₃ @Ti ₂ Se/p-Si devices. Journal of Materials Science: Materials in Electronics, 2018, 29, 12561-12572.	1.1	24
43	Frequency and electric field controllable photodevice: FYTRONIX device. Physica B: Condensed Matter, 2017, 519, 53-58.	1.3	16
44	A functional material based photodiode for solar tracking systems. Physica B: Condensed Matter, 2017, 520, 76-81.	1.3	18
45	Electrical Properties of Dilute Nitride GaAsPN/GaPN MQW p-n Diode. Journal of Electronic Materials, 2017, 46, 4590-4595.	1.0	5
46	A photodiode based on PbS nanocrystallites for FYTRONIX solar panel automatic tracking controller. Physica B: Condensed Matter, 2017, 527, 44-51.	1.3	19
47	Frequency and voltage dependence of dielectric properties, complex electric modulus, and electrical conductivity in Au/7% graphene doped@PVA/n-Si (MPS) structures. Journal of Applied Polymer Science, 2016, 133, .	1.3	47
48	Analysis of interface states of FeO-Al ₂ O ₃ spinel composite film/p-Si diode by conductance technique. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	26
49	Single crystal ruthenium(II) complex dye based photodiode. Dyes and Pigments, 2016, 132, 64-71.	2.0	46
50	A new shape memory alloy film/p-Si solar light four quadrant detector for solar tracking applications. Journal of Alloys and Compounds, 2016, 688, 762-768.	2.8	35
51	Thermal sensors based on delafossite film/p-silicon diode for low-temperature measurements. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	16
52	Photoresponse and photocapacitor properties of Au/AZO/p-Si/Al diode with AZO film prepared by pulsed laser deposition (PLD) method. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	37
53	Graphene-cobalt phthalocyanine based on optoelectronic device for solar panel tracking systems. Synthetic Metals, 2015, 206, 15-23.	2.1	30
54	Photodiode and photocapacitor properties of Au/CdTe/p-Si/Al device. Journal of Alloys and Compounds, 2015, 646, 1151-1156.	2.8	59

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55	Composite metal oxide semiconductor based photodiodes for solar panel tracking applications. Journal of Alloys and Compounds, 2015, 650, 692-699.	2.8	12
56	A novel type heterojunction photodiodes formed junctions of Au/LiZnSnO and LiZnSnO/p-Si in series. Journal of Alloys and Compounds, 2015, 625, 18-25.	2.8	44
57	Ferroelectric Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ photodiode for solar cell applications. Solar Energy Materials and Solar Cells, 2015, 133, 69-75.	3.0	31
58	Effects of Temperature on Dielectric Parameters of Metal-Oxide-Semiconductor Capacitor with Thermal Oxide Layer. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 675-679.	0.1	5
59	Effects of gamma irradiation on electrical parameters of metal-insulator-semiconductor structure with silicon nitride interfacial insulator layer. Radiation Effects and Defects in Solids, 2014, 169, 791-799.	0.4	14
60	Dielectric characteristics of gamma irradiated Au/SnO ₂ /n-Si/Au (MOS) capacitor. Materials Science in Semiconductor Processing, 2014, 28, 89-93.	1.9	12
61	Photoconducting properties of Cd _{0.4} Zn _{0.6} /p-Si photodiode by sol gel method. Journal of Electroceramics, 2014, 32, 369-375.	0.8	18
62	Electrical and photoconducting properties of nanorod in based spinel compound/p-Si photodiode by sol-gel spin coating technique. Journal of Sol-Gel Science and Technology, 2014, 71, 421-427.	1.1	11
63	Analysis of Electrical Characteristics of Metal-Oxide-Semiconductor Capacitor by Impedance Spectroscopy. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 515-519.	0.1	6
64	The Richardson constant and barrier inhomogeneity at Au/Si ₃ N ₄ /n-Si (MIS) Schottky diodes. Physica Scripta, 2013, 88, 015801.	1.2	47
65	Temperature-dependent dielectric properties of Au/Si ₃ N ₄ /n-Si (metal-insulator-semiconductor) structures. Chinese Physics B, 2013, 22, 117310.	0.7	18
66	Determination of interface states and their time constant for Au/SnO ₂ /n-Si (MOS) capacitors using admittance measurements. Chinese Physics B, 2013, 22, 047303.	0.7	29
67	Comparative study of the electrical properties of Au/n-Si (MS) and Au/Si ₃ N ₄ /n-Si (MIS) Schottky diodes. Chinese Physics B, 2013, 22, 068402.	0.7	41
68	Analysis of the series resistance and interface states of Au/Si ₃ N ₄ /n-Si (metal-insulator-semiconductor) Schottky diodes using $I-V$ characteristics in a wide temperature range. Physica Scripta, 2012, 86, 035802.	1.2	39
69	Influence of Temperature and Frequency on Dielectric Permittivity and ac Conductivity of Au/SnO ₂ /n-Si (MOS) Structures. Chinese Physics Letters, 2012, 29, 077304.	1.3	46
70	On the temperature dependent dielectric properties, conductivity and resistivity of MIS structures at 1MHz. Microelectronic Engineering, 2012, 91, 154-158.	1.1	40
71	The density of interface states and their relaxation times in Au/Bi ₄ Ti ₃ O ₁₂ /SiO ₂ /n-Si (MFIS) structures. Surface and Interface Analysis, 2011, 43, 1561-1565.	0.8	27
72	The role of ⁶⁰ Co γ -ray irradiation on the interface states and series resistance in MIS structures. Radiation Physics and Chemistry, 2010, 79, 457-461.	1.4	16

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73	Analysis of surface states and series resistance in Au/n-Si Schottky diodes with insulator layer using current-voltage and admittance-voltage characteristics. Vacuum, 2009, 84, 363-368.	1.6	55
74	Gamma-ray irradiation effects on the interface states of MIS structures. Sensors and Actuators A: Physical, 2009, 151, 168-172.	2.0	11
75	The distribution of barrier heights in MIS type Schottky diodes from current-voltage-temperature ($I-V-T$) measurements. Journal of Alloys and Compounds, 2009, 479, 893-897.	2.8	67
76	The analysis of the series resistance and interface states of MIS Schottky diodes at high temperatures using $I-V$ characteristics. Journal of Alloys and Compounds, 2009, 484, 405-409.	2.8	93
77	On the profile of frequency dependent series resistance and surface states in Au/Bi ₄ Ti ₃ O ₁₂ /SiO ₂ /n-Si(MFIS) structures. Microelectronic Engineering, 2008, 85, 81-88.	1.1	74
78	The interface states analysis of the MIS structure as a function of frequency. Microelectronic Engineering, 2008, 85, 542-547.	1.1	9
79	On the energy distribution of interface states and their relaxation time and capture cross section profiles in Al/SiO ₂ /p-Si (MIS) Schottky diodes. Microelectronic Engineering, 2008, 85, 1495-1501.	1.1	68
80	Dielectric properties and ac electrical conductivity studies of MIS type Schottky diodes at high temperatures. Microelectronic Engineering, 2008, 85, 1518-1523.	1.1	52
81	Study on the frequency dependence of electrical and dielectric characteristics of Au/SnO ₂ /n-Si (MIS) structures. Microelectronic Engineering, 2008, 85, 1866-1871.	1.1	35
82	Analysis of electrical characteristics of Au/SiO ₂ /n-Si (MOS) capacitors using the high-low frequency capacitance and conductance methods. Microelectronic Engineering, 2008, 85, 2256-2260.	1.1	78
83	The effect of ⁶⁰ Co (γ -ray) irradiation on the electrical characteristics of Au/SnO ₂ /n-Si (MIS) structures. Radiation Physics and Chemistry, 2008, 77, 74-78.	1.4	23
84	Characterization of interface states at Au/SnO ₂ /n-Si (MOS) structures. Vacuum, 2008, 82, 1203-1207.	1.6	35
85	The temperature profile and bias dependent series resistance of Au/Bi ₄ Ti ₃ O ₁₂ /SiO ₂ /n-Si (MFIS) structures. Vacuum, 2008, 82, 1246-1250.	1.6	21
86	Analysis of interface states and series resistance of MIS Schottky diodes using the current-voltage ($I-V$) characteristics. Microelectronic Engineering, 2008, 85, 233-237.	1.1	61
87	Frequency and voltage effects on the dielectric properties and electrical conductivity of Al-Ti-W-Pd ₂ Si/n-Si structures. Microelectronic Engineering, 2008, 85, 247-252.	1.1	106
88	Analysis of interface states and series resistance at MIS structure irradiated under ⁶⁰ Co γ -rays. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2007, 580, 1588-1593.	0.7	15
89	Effects of beta-ray irradiation on the $C-V$ and G/V characteristics of Au/SiO ₂ /n-Si (MOS) structures. Nuclear Instruments & Methods in Physics Research B, 2007, 254, 273-277.	0.6	5
90	Irradiation effect on dielectric properties and electrical conductivity of Au/SiO ₂ /n-Si (MOS) structures. Nuclear Instruments & Methods in Physics Research B, 2007, 264, 73-78.	0.6	6

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91	The barrier height distribution in identically prepared Al/p-Si Schottky diodes with the native interfacial insulator layer (SiO ₂). Physica B: Condensed Matter, 2007, 399, 146-154.	1.3	41
92	On the profile of frequency dependent series resistance and dielectric constant in MIS structure. Microelectronic Engineering, 2007, 84, 180-186.	1.1	67
93	The effects of frequency and $\hat{\text{I}}^3$ -irradiation on the dielectric properties of MIS type Schottky diodes. Nuclear Instruments & Methods in Physics Research B, 2007, 254, 113-117.	0.6	15
94	Electrical and dielectric properties of MIS Schottky diodes at low temperatures. Microelectronic Engineering, 2006, 83, 2551-2557.	1.1	61
95	^{60}Co $\hat{\text{I}}^3$ irradiation effects on the current-voltage (I-V) characteristics of Al/SiO ₂ /p-Si (MIS) Schottky diodes. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2006, 568, 863-868.	0.7	36
96	Electrical characteristics of ^{60}Co $\hat{\text{I}}^3$ -ray irradiated MIS Schottky diodes. Nuclear Instruments & Methods in Physics Research B, 2006, 252, 257-262.	0.6	36
97	Characterization of current-voltage (I-V) and capacitance-voltage-frequency (C-V-f) features of Al/SiO ₂ /p-Si (MIS) Schottky diodes. Microelectronic Engineering, 2006, 83, 582-588.	1.1	114
98	The C-V-f and G/f-V-f characteristics of Al/SiO ₂ /p-Si (MIS) structures. Microelectronic Engineering, 2006, 83, 2021-2026.	1.1	49
99	Density of interface states, excess capacitance and series resistance in the metal-insulator-semiconductor (MIS) solar cells. Solar Energy Materials and Solar Cells, 2005, 85, 345-358.	3.0	79
100	The effect of interface states, excess capacitance and series resistance in the Al/SiO ₂ /p-Si Schottky diodes. Applied Surface Science, 2005, 252, 1732-1738.	3.1	80
101	Dielectric properties in Au/SnO ₂ /n-Si (MOS) structures irradiated under ^{60}Co - $\hat{\text{I}}^3$ rays. Microelectronics Journal, 2004, 35, 731-738.	1.1	14
102	Au/SnO ₂ /n-Si (MOS) structures response to radiation and frequency. Microelectronics Journal, 2003, 34, 1043-1049.	1.1	43
103	The role of interface states and series resistance on the I-V and C-V characteristics in Al/SnO ₂ /p-Si Schottky diodes. Solid-State Electronics, 2003, 47, 1847-1854.	0.8	192